

Figure 1. (a) X-ray diffraction measurements of 53 nm thick β -Ga₂O₃ on NbN_x on-axis 6H-SiC. (b) TEM of this β -Ga₂O₃ layer on NbN_x/6H-SiC with clear interfaces. (c) High resolution TEM image β -Ga₂O₃/NbN_x interface.

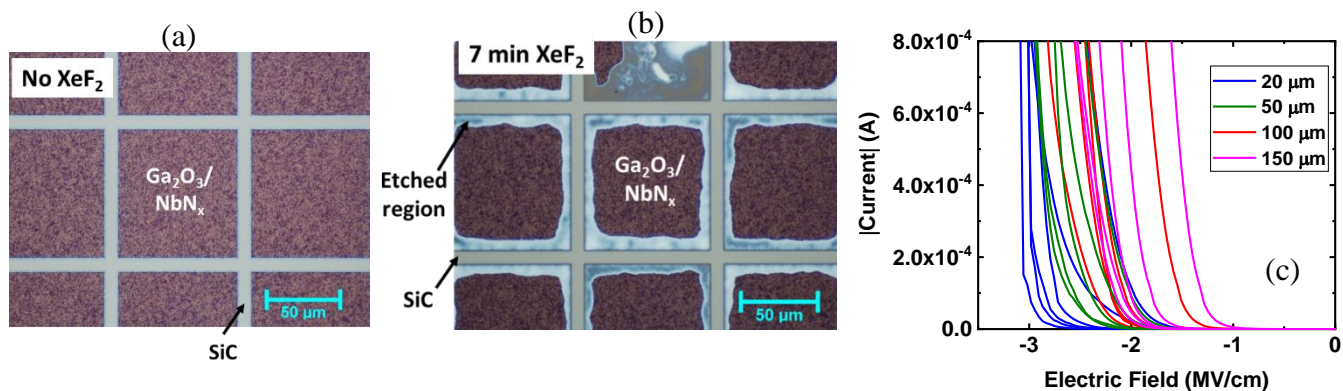


Figure 2. Optical image of Ga₂O₃ on NbN_x/SiC showing undercut (a) before and (b) after etching of buried NbN_x layer in Xef₂. (c) Electrical breakdown field of Ga₂O₃ on NbN_x/SiC.